

In the Claims:

Claim 1 (original): A method for forming a field effect transistor over a substrate, said method comprising steps of:

forming an interfacial oxide layer over a channel region of said substrate, said interfacial oxide layer having a first thickness;

forming an oxygen-attracting layer over said interfacial oxide layer;

forming a high-k dielectric layer over said oxygen-attracting layer;

forming a gate electrode layer over said high-k dielectric layer;

wherein said oxygen-attracting layer prevents said first thickness of said interfacial oxide layer from increasing.

Claim 2 (original): The method of claim 1 wherein said interfacial oxide layer prevents a high-k element from diffusing into said channel region.

Claim 3 (original): The method of claim 1 wherein said step of forming said oxygen-attracting layer comprises forming a metal layer over said interfacial oxide layer, said metal layer combining with oxygen to form a silicate.

Claim 4 (original): The method of claim 1 wherein said oxygen-attracting layer is selected from the group consisting of zirconium silicate and hafnium silicate.

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Claim 5 (original): The method of claim 1 wherein said high-k dielectric layer is selected from the group consisting of hafnium oxide, hafnium silicate, zirconium silicate, and zirconium oxide.

Claim 6 (original): The method of claim 1 wherein said first thickness of said interfacial oxide layer is between approximately 4.0 Angstroms and approximately 5.0 Angstroms.

Claim 7 (original): The method of claim 1 wherein a second thickness of said oxygen-attracting layer is approximately 5.0 Angstroms.

Claims 8-20 (canceled).